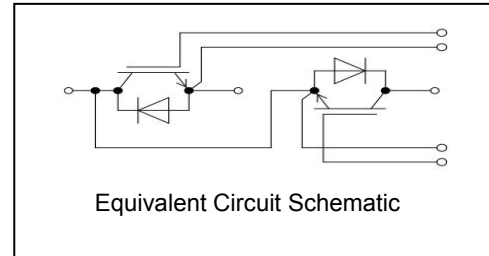


**IGBT MODULE 2-PACK TYPE****Features**

- $I_c=300A$
- Ultrafast switching speed
- Excellent short circuit ruggedness
- Low conduction loss

**Typical Applications**

- IGBTs offer ultrafast switching speed for application such as Welding, inductive heating, UPS and other high frequency Application.

**Absolute Maximum Ratings**

$V_{CES}$	Collector to Emitter Voltage		1200	V
$V_{GES}$	Continuous Gate to Emitter Voltage		+/-30	V
$I_C$	Continuous Collector Current	$T_C=25^\circ C$	600	A
		$T_C=100^\circ C$	300	
$I_{CM}$	Pulse Collector Current	$T_J=150^\circ C$	600	A
$P_D$	Maximum Power Dissipation(IGBT)	$T_C=25^\circ C$	1080	W
$t_{sc}$	Short Circuit Withstand Time		> 10	$\mu s$
$T_J$	Maximum IGBT Junction Temperature		-40~+150	$^\circ C$
$T_{JOP}$	Maximum Operating Junction temperature Rang		-40~+150	$^\circ C$
$T_{stg}$	Storage Temperature Range		-40~+125	$^\circ C$

## Electrical Characteristics at T<sub>J</sub>=25°C (Unless Otherwise Specified)

Parameter		Test Condition	Min.	Typ.	Max.	Unit
BV <sub>CES</sub>	Collector to Emitter Breakdown Voltage	V <sub>GE</sub> =0V, I <sub>C</sub> =1mA	1200			V
I <sub>CES</sub>	Collector to Emitter Leakage Current	V <sub>GE</sub> =0V, V <sub>CE</sub> =V <sub>CES</sub>			1	mA
I <sub>GES</sub>	Gate to Emitter Leakage Current	V <sub>GE</sub> = +/-30V, V <sub>CE</sub> =0V			1000	nA
V <sub>GE(th)</sub>	Gate Threshold Voltage	I <sub>C</sub> =1mA, V <sub>CE</sub> =V <sub>GE</sub>	5.0		7.0	V
V <sub>CE(sat)</sub>	Collector to Emitter Saturation Voltage (Module Level)	I <sub>C</sub> =300A T <sub>J</sub> =25°C V <sub>GE</sub> =15V		1.65	1.90	V

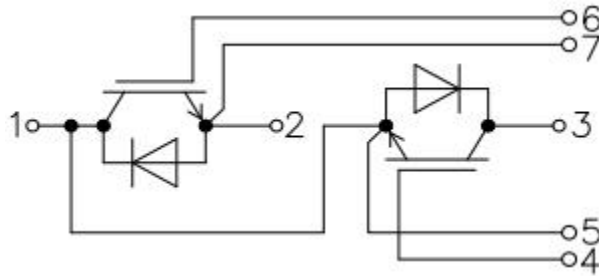
## Switching Characteristics

t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>CC</sub> =600V I <sub>C</sub> =300A R <sub>G</sub> =10Ω V <sub>GE</sub> =+/-15V Inductive Load	T <sub>J</sub> =25°C		440		ns
			T <sub>J</sub> =125°C		510		
t <sub>r</sub>	Turn-on Rise Time		T <sub>J</sub> =25°C		560		ns
			T <sub>J</sub> =125°C		630		
t <sub>d(off)</sub>	Turn-off Delay Time		T <sub>J</sub> =25°C		850		ns
			T <sub>J</sub> =125°C		960		
t <sub>f</sub>	Turn-off Fall Time		T <sub>J</sub> =25°C		250		ns
			T <sub>J</sub> =125°C		300		
E <sub>on</sub>	Turn-on Switching Loss		T <sub>J</sub> =25°C		8.2		mJ
			T <sub>J</sub> =125°C		9.5		
E <sub>off</sub>	Turn-off Switching Loss	T <sub>J</sub> =25°C		22.3		mJ	
		T <sub>J</sub> =125°C		34			
Q <sub>g</sub>	Total Gate Charge		T <sub>J</sub> =25°C		920		nC
R <sub>gint</sub>	Integrated Gate Resistor	f=1M, V <sub>pp</sub> =1V	T <sub>J</sub> =25°C		9.50		Ω
C <sub>ies</sub>	Input Capacitance	V <sub>CE</sub> =25V V <sub>GE</sub> =0V f=1MHZ	T <sub>J</sub> =25°C		28000		pF
C <sub>oes</sub>	Output Capacitance		T <sub>J</sub> =25°C		1220		
C <sub>res</sub>	Reverse Transfer capacitance		T <sub>J</sub> =25°C		1850		
R <sub>jc</sub>	Thermal Resistance, Junction-to-Case					0.11	°C/W

**Module Characteristics**

Parameter		Min.	Typ.	Max.	Unit
Viso	Isolation Voltage(All terminals Shorted) f=50Hz, 1Minute	2500		3000	V
Rcs	Case-to-Sink(Conductive Grease Applied)		0.05		°C/W
M	Power Terminals Screw M6	4.0		6.0	Nm
M	Mounting Screw M6	4.0		6.0	Nm
G	Weight		300		g

### Internal Circuit:



### Package Dimension in Millimeter

